

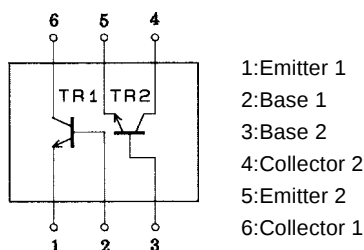


FC152

PNP Epitaxial Planar Silicon Composite Transistor High-Frequency Amp, Differential Amp Applications

Features

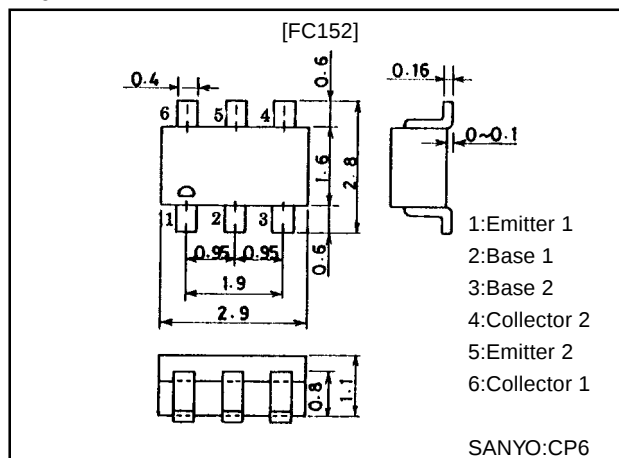
- Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC152 is formed with two chips, being equivalent to the 2SC4270, placed in one package.
- Excellent in thermal equilibrium, pair capability and especially suited for differential amp.



Package Dimensions

unit:mm

2104A



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		25	V
Collector-to-Emitter Voltage	V_{CEO}		15	V
Emitter-to-Base Voltage	V_{EBO}		3	V
Collector Current	I_C		50	mA
Collector Dissipation	P_C	1 unit	200	mW
Total Dissipation	P_T		300	mW
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CB0}	$V_{CB}=20\text{V}, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=2\text{V}, I_C=0$			10	μA
DC Current Gain	h_{FE}	$V_{CE}=10\text{V}, I_C=5\text{mA}$	60		200	
DC Current Gain Ratio	$h_{FE}(\text{small/large})$	$V_{CE}=10\text{V}, I_C=5\text{mA}$	0.7	0.95		
B-E Voltage Difference	$V_{BE}(\text{large-small})$	$V_{CE}=10\text{V}, I_C=0$		3.0	10	mV
Gain-Bandwidth Product	f_T	$V_{CE}=10\text{V}, I_C=10\text{mA}$	1.5	3.0		GHz
Output Capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$		0.7	1.0	pF
Power Gain	PG	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=0.9\text{GHz}$		12		dB
Noise Figure	NF	$V_{CE}=10\text{V}, I_C=3\text{mA}, f=0.9\text{GHz}$		3.0		dB

Note: The specifications shown above are for each individual transistor. However, the specifications of $h_{FE}(\text{small/large})$ and $V_{BE}(\text{large-small})$ are for pair capability

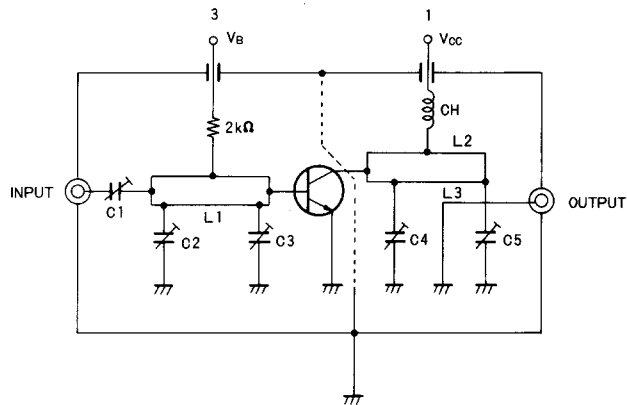
Marking:152

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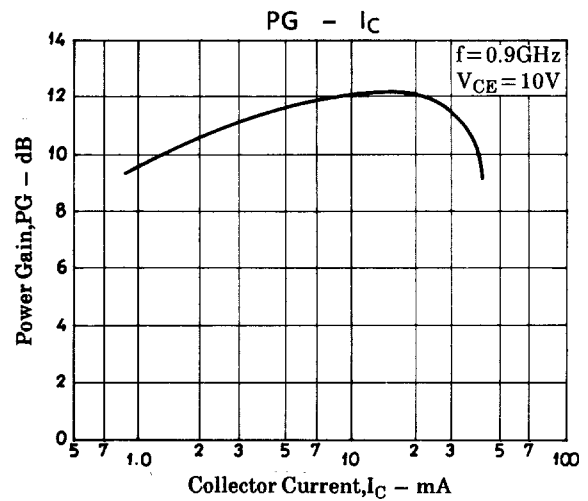
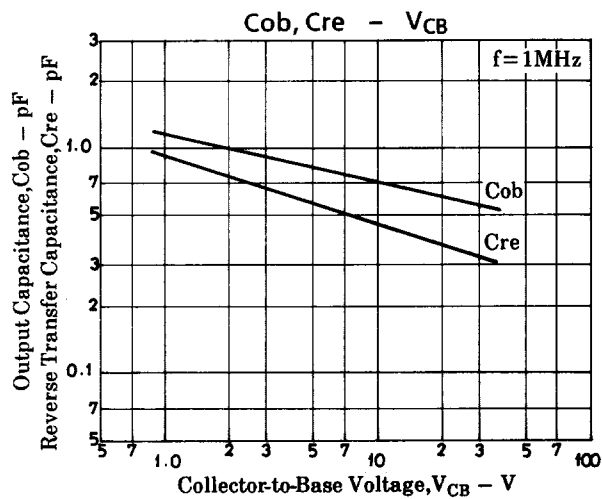
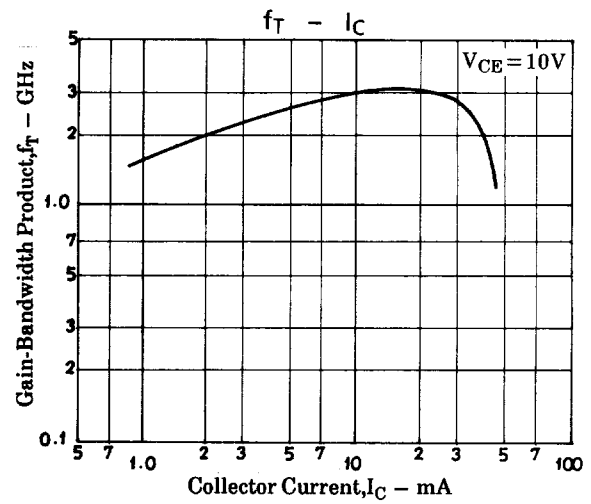
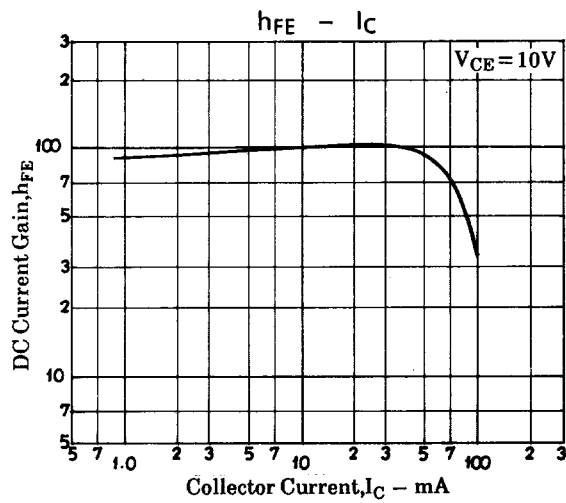
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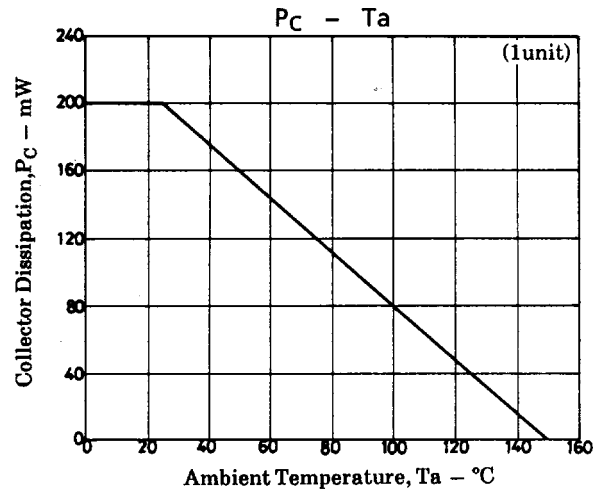
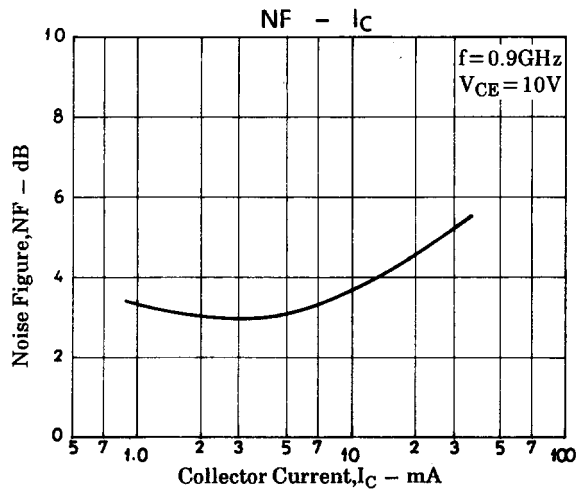
PG, NF Test Circuit



900MHz	
C1	~5pF
C2	~10pF
C3	~10pF
C4	~10pF
C5	~10pF
L1	W≅1.5mm, l≅25mm strip line
L2	W≅4mm, l≅25mm strip line
L3	0.5φ, l≅40mm
CH	2t + bead core



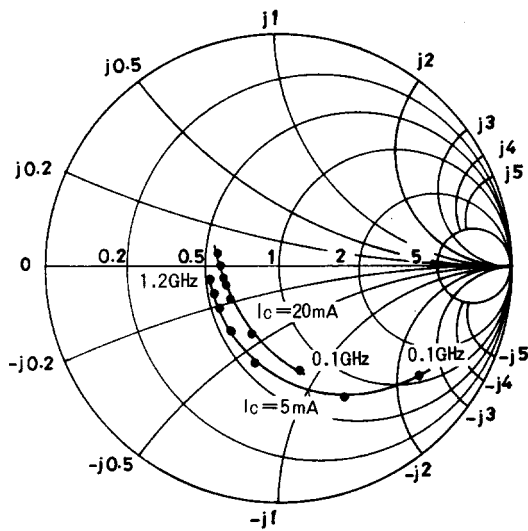
FC152



S Parameter

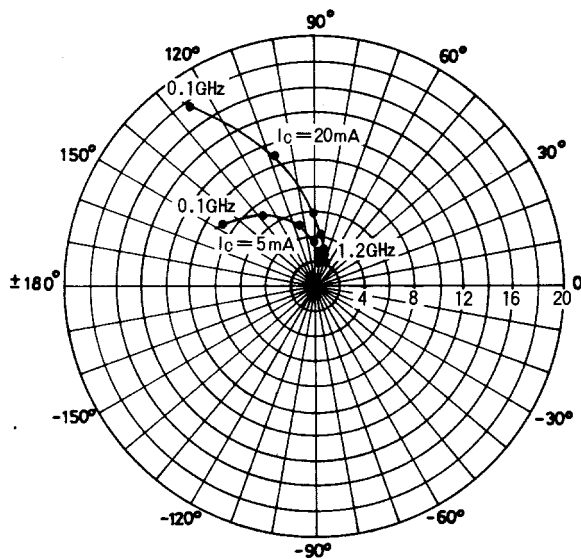
S11e: $V_{CE} = 10\text{V}$

$f = 100\text{MHz}$, 200 to 1200MHz (200MHz step)



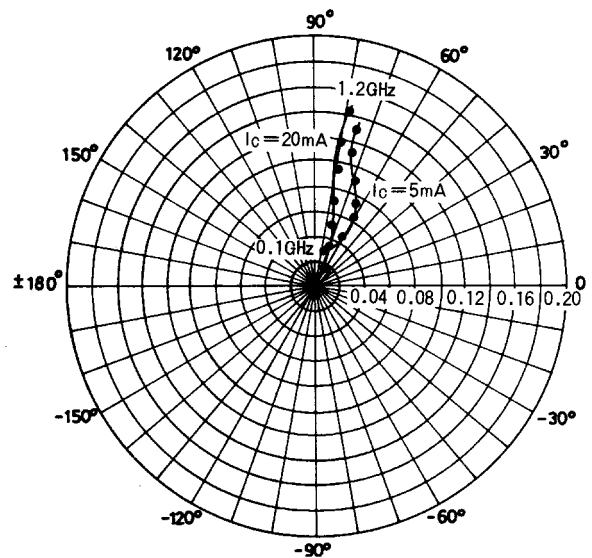
S21e: $V_{CE} = 10\text{V}$

$f = 100\text{MHz}$, 200 to 1200MHz (200MHz step)



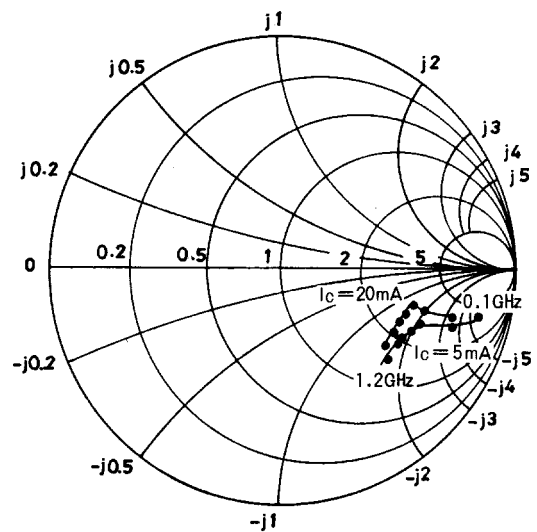
S12e: $V_{CE} = 10\text{V}$

$f = 100\text{MHz}$, 200 to 1200MHz (200MHz step)



S22e: $V_{CE} = 10\text{V}$

$f = 100\text{MHz}$, 200 to 1200MHz (200MHz step)



S Parameter (Common-emitter) $V_{CE} = 10V, I_C = 5mA, Z_0 = 50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.771	-35.1	8.763	147.2	0.027	69.3	0.890	-14.2
200	0.613	-64.7	7.004	127.6	0.043	59.8	0.780	-19.7
400	0.429	-110.7	4.882	103.1	0.061	58.1	0.660	-22.8
600	0.361	-133.5	3.471	90.5	0.075	63.1	0.625	-25.1
800	0.355	-148.4	2.693	81.6	0.091	68.1	0.612	-28.6
900	0.331	-153.7	2.450	78.9	0.100	70.5	0.609	-29.9
1000	0.328	-158.9	2.236	75.5	0.110	72.5	0.607	-31.6
1200	0.326	-167.9	1.932	69.9	0.130	74.7	0.608	-35.7

 $V_{CE} = 10V, I_C = 20mA, Z_0 = 50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
100	0.447	-78.1	17.728	125.0	0.020	66.0	0.752	-18.5
200	0.338	-113.2	10.936	107.5	0.031	66.5	0.639	-18.5
400	0.290	-146.6	5.773	91.4	0.052	72.1	0.580	-18.5
600	0.281	-159.3	3.956	83.0	0.074	75.7	0.571	-21.1
800	0.285	-168.8	2.982	76.2	0.095	77.6	0.566	-25.2
900	0.289	-171.3	2.703	74.0	0.106	78.6	0.563	-26.7
1000	0.291	-174.4	2.454	71.3	0.118	79.4	0.565	-28.6
1200	0.297	-178.1	2.116	66.5	0.140	79.0	0.569	-33.1

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